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AMENDMENTS TO THE ABSTRACT:

A light emitting diode (LED) structure and manufacture method thereof are disclosed, whercin a buffer layer is grown on a substrate and then an LED structural layer is grown on the buffer layer. The LED structural layer comprises a p-type quantum-dot epitaxial layer on a p-type GaN layer. As the p-type quantum-dot epitaxial layer has a coarsening and scattering effect, the path of light emitted from an InGaN multiple-quantum-well structural layer is changed. Therefore, it is possible to decrease lessen the probability of total reflection and thereby increase heighten the light-emitting efficiency of LED.